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Sommario/riassunto

Almost all the semiconductors of practical interest are the group-IV, III-V and II-VI semiconductors and the range of technical applications of such semiconductors is extremely wide. The purpose of this book is twofold: * to discuss the key properties of the group-IV, III-V and II-VI semiconductors* to systemize these properties from a solid-state physics aspect. The majority of the text is devoted to the description of the lattice structural, thermal, elastic, lattice dynamic, electronic energy-band structural, optical and carrier transport properties of these semiconductors. Some
